

## P-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- ✓ Advanced trench cell design
- ✓ Low Thermal Resistance

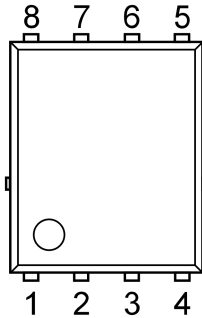
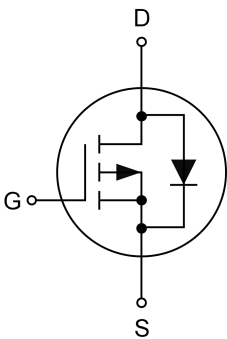
#### 1.2 Applications

- ✓ Motor drivers
- ✓ DC-DC Converter

#### 1.3 Quick reference

- ✓  $BV \geq -30\text{ V}$
- ✓  $P_D \leq 50\text{ W}$
- ✓  $I_D \leq -80\text{ A}$
- ✓  $R_{DS(ON)} \leq 7.5\text{ m}\Omega @V_{GS} = -10\text{ V}$
- ✓  $R_{DS(ON)} \leq 12\text{ m}\Omega @V_{GS} = -4.5\text{ V}$

### 2. Pin Description

| Pin     | Description | Simplified Outline                                                                                                  | Symbol                                                                                |
|---------|-------------|---------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| 1,2,3   | Source      |  <p>Top View<br/>PDFN5x6-8L</p> |  |
| 4       | Gate        |                                                                                                                     |                                                                                       |
| 5,6,7,8 | Drain       |                                                                                                                     |                                                                                       |

## 3. Limiting Values

| Symbol                | Parameter                                        | Conditions                                     | Min | Max      | Unit                 |
|-----------------------|--------------------------------------------------|------------------------------------------------|-----|----------|----------------------|
| $V_{DS}$              | Drain-Source Voltage                             | $T_A=25^{\circ}\text{C}$                       | -30 | -        | V                    |
| $V_{GS}$              | Gate-Source Voltage                              | $T_A=25^{\circ}\text{C}$                       | -   | $\pm 20$ | V                    |
| $I_D^{*, **}$         | Drain Current (DC)                               | $T_A=25^{\circ}\text{C}, V_{GS}=-10\text{ V}$  | -   | -80      | A                    |
|                       |                                                  | $T_A=100^{\circ}\text{C}, V_{GS}=-10\text{ V}$ | -   | -63      | A                    |
| $I_{DM}^{*, **, ***}$ | Drain Current (Pulsed)                           | $T_A=25^{\circ}\text{C}, V_{GS}=-10\text{ V}$  | -   | -360     | A                    |
| $P_D^*$               | Drain power dissipation                          | $T_A=25^{\circ}\text{C}$                       | -   | 79       | W                    |
| $I_S$                 | Continuous-Source Current                        | $T_A=25^{\circ}\text{C}$                       | -   | -80      | A                    |
| $E_{AS}^*$            | Single Pulsed Avalanche Energy                   | $V_{DD}=-15\text{ V}, L=0.5\text{ mH}$         | -   | 269      | mJ                   |
| $T_J, T_{stg}$        | Operating Junction and Storage Temperature Range |                                                | -55 | 150      | $^{\circ}\text{C}$   |
| $R_{\theta JA}$       | Thermal Resistance, Junction to Ambient          |                                                | -   | 62.5     | $^{\circ}\text{C/W}$ |
| $R_{\theta JC}$       | Thermal Resistance, Junction to Case             |                                                | -   | 2.5      |                      |

Notes:

- \* Surface mounted on 1 in<sup>2</sup> pad area,  $t \leq 10\text{ sec}$ .
- \*\* Pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- \*\*\* Limited by bonding wire.

## 4. Marking Information

| Product Name | Marking         |
|--------------|-----------------|
| KJ80P03G     | 80P03<br>XXXXXX |

## 5. Ordering Code

| Product Name | Package     | Reel size | Tape width | Quantity (pcs) |
|--------------|-------------|-----------|------------|----------------|
| KJ80P03G     | PDFN 5x6-8L | 13"       | 12 mm      | 5000           |

Note: KUAJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C).

## 6. Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

| Symbol                                   | Parameter                      | Conditions                                                                                        | Min  | Typ  | Max  | Unit |
|------------------------------------------|--------------------------------|---------------------------------------------------------------------------------------------------|------|------|------|------|
| Static Characteristics                   |                                |                                                                                                   |      |      |      |      |
| BV <sub>DSS</sub>                        | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0 V, I <sub>DS</sub> =-250 μA                                                    | -30  | -    | -    | V    |
| V <sub>GS(th)</sub>                      | Gate Threshold Voltage         | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =-250 μA                                       | -1.0 | -1.5 | -2.0 | V    |
| I <sub>DSS</sub>                         | Drain Leakage Current          | V <sub>DS</sub> =-30 V, V <sub>GS</sub> =0 V                                                      | -    | -    | -1   | μA   |
| I <sub>GSS</sub>                         | Gate Leakage Current           | V <sub>GS</sub> =±20 V, V <sub>DS</sub> =0 V                                                      | -    | -    | ±100 | nA   |
| R <sub>DS(ON)</sub> <sup>a</sup>         | On-State Resistance            | V <sub>GS</sub> =-10 V, I <sub>D</sub> =-30 A                                                     | -    | 5.8  | 7.5  | mΩ   |
|                                          |                                | V <sub>GS</sub> =-4.5 V, I <sub>D</sub> =-20 A                                                    | -    | 9    | 12   |      |
| Diode Characteristics                    |                                |                                                                                                   |      |      |      |      |
| V <sub>SD</sub> <sup>a</sup>             | Diode Forward Voltage          | I <sub>SD</sub> =-1A, V <sub>GS</sub> =0 V                                                        | -    | -    | -1.2 | V    |
| Dynamic Characteristics <sup>b</sup>     |                                |                                                                                                   |      |      |      |      |
| C <sub>iss</sub>                         | Input Capacitance              | V <sub>GS</sub> =0 V, V <sub>DS</sub> =-15 V, Frequency=1 MHz                                     | -    | 4320 | -    | pF   |
| C <sub>oss</sub>                         | Output Capacitance             |                                                                                                   | -    | 534  | -    |      |
| C <sub>rss</sub>                         | Reverse Transfer Capacitance   |                                                                                                   | -    | 493  | -    |      |
| t <sub>d(on)</sub>                       | Turn-on Delay Time             | V <sub>DS</sub> =-15 V, I <sub>DS</sub> =-15 A<br>V <sub>GEN</sub> =-10 V, R <sub>G</sub> =2.5 Ω, | -    | 19   | -    | ns   |
| t <sub>r</sub>                           | Turn-on Rise Time              |                                                                                                   | -    | 15   | -    |      |
| t <sub>d(off)</sub>                      | Turn-off Delay Time            |                                                                                                   | -    | 65   | -    |      |
| t <sub>f</sub>                           | Turn-off Fall Time             |                                                                                                   | -    | 36   | -    |      |
| Gate Charge Characteristics <sup>b</sup> |                                |                                                                                                   |      |      |      |      |
| Q <sub>g</sub>                           | Total Gate Charge              | V <sub>GS</sub> =-10 V, V <sub>DS</sub> =-15 V, I <sub>DS</sub> =-15 A                            | -    | 45   | -    | nC   |
| Q <sub>gs</sub>                          | Gate-Source Charge             |                                                                                                   | -    | 8    | -    |      |
| Q <sub>gd</sub>                          | Gate-Drain Charge              |                                                                                                   | -    | 12   | -    |      |

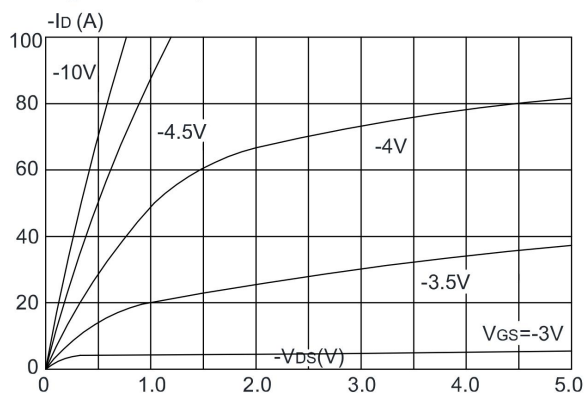
Notes :

a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2%

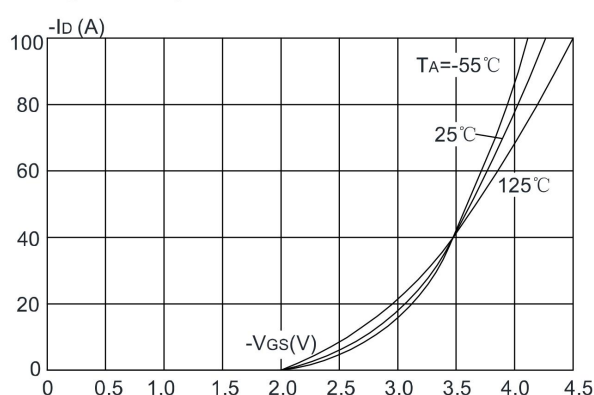
b : Guaranteed by design, not subject to production testing

## 7. Typical Characteristics

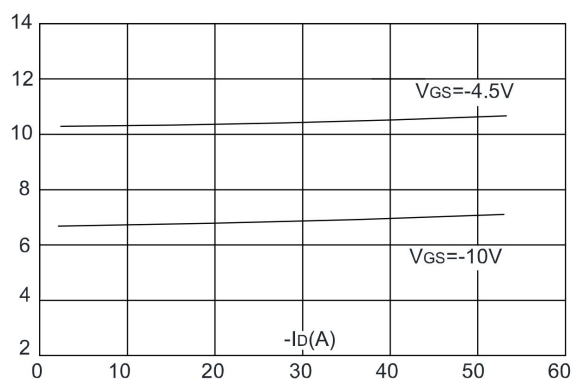
**Figure1: Output Characteristics**



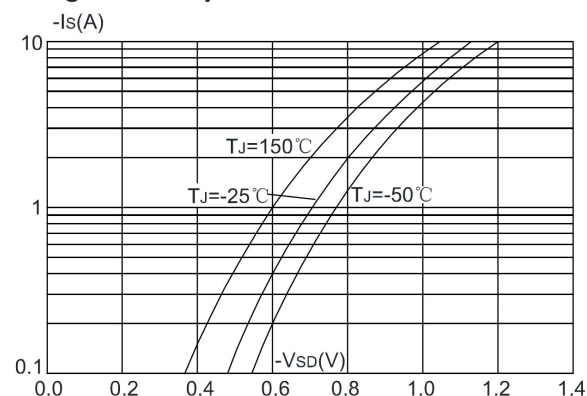
**Figure 2: Typical Transfer Characteristics**



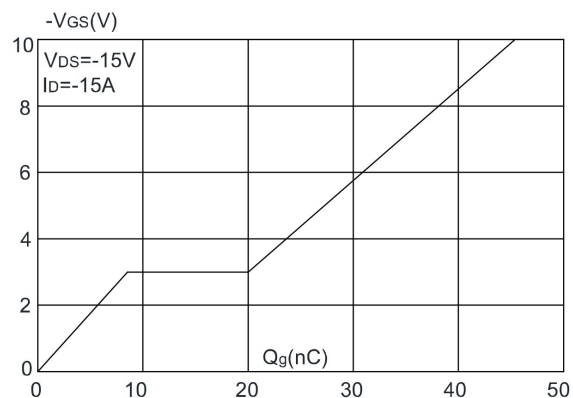
**Figure 3: On-resistance vs. Drain Current**



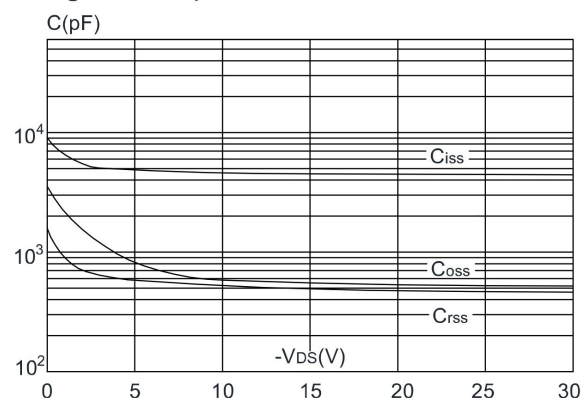
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

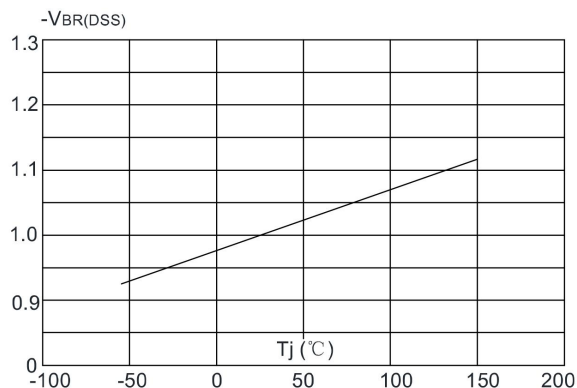


**Figure 6: Capacitance Characteristics**

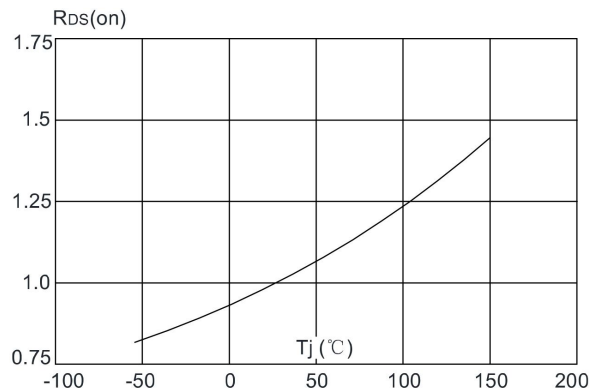


## 7. Typical Characteristics (cont.)

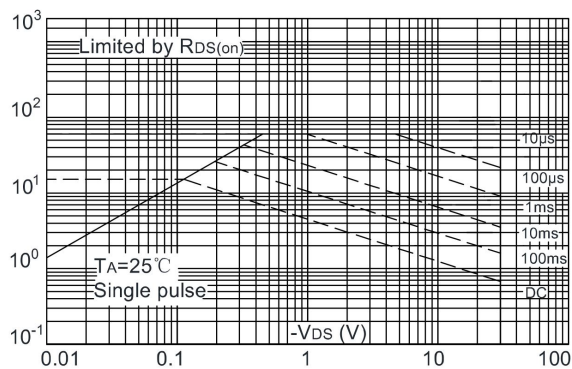
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



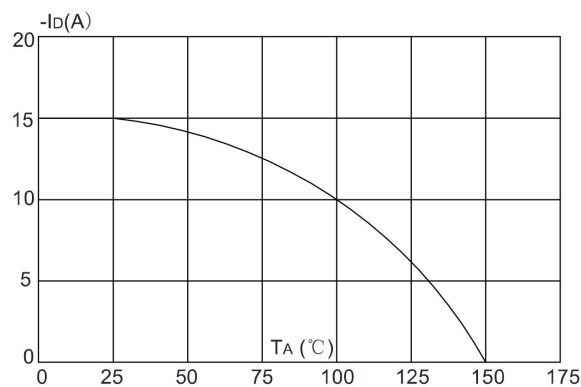
**Figure 8:** Normalized on Resistance vs. Junction Temperature



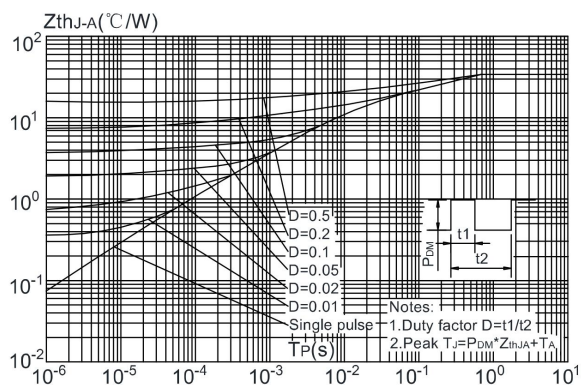
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

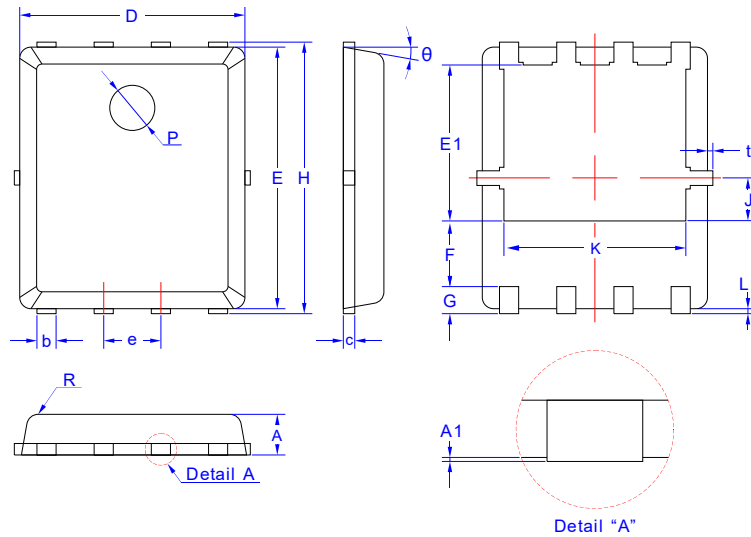


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



## 8. Package Dimensions

PDFN 5×6-8L Package



| Symbol | Dimensions in Millimeters |      |
|--------|---------------------------|------|
|        | MIN                       | MAX  |
| A      | 0.80                      | 1.00 |
| A1     | 0.00                      | 0.05 |
| b      | 0.35                      | 0.49 |
| c      | 0.254 REF                 |      |
| D      | 4.90                      | 5.10 |
| E      | 5.70                      | 5.90 |
| E1     | 3.40 REF                  |      |
| e      | 1.27 BSC                  |      |
| F      | 1.40 REF                  |      |
| G      | 0.60 REF                  |      |
| H      | 5.95                      | 6.20 |
| J      | 0.95 BSC                  |      |
| K      | 4.00 REF                  |      |
| L1     | 0.10                      | 0.18 |
| L      | -                         | 0.15 |
| P      | 1.00 REF                  |      |
| R      | 0.25 REF                  |      |
| θ      | 6°                        | 14°  |